

RJE0603JPE

Silicon P Channel MOS FET Series Power Switching

R07DS0193EJ0200
(Previous: REJ03G1907-0100)
Rev.2.00
Nov 04, 2010

Description

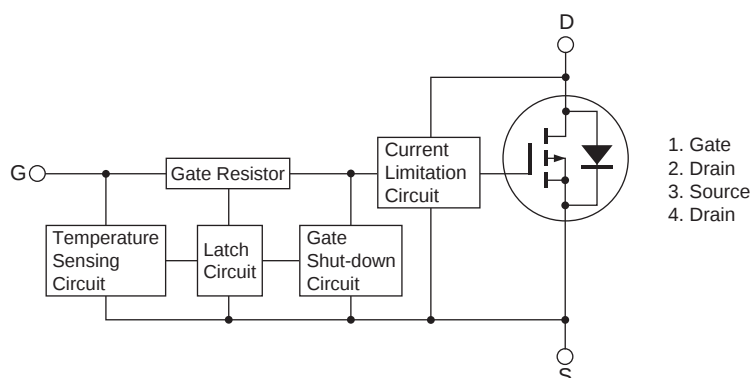
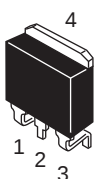
This FET has the over temperature shut-down capability sensing to the junction temperature. This FET has the built-in over temperature shut-down circuit in the gate area. And this circuit operation to shut-down the gate voltage in case of high junction temperature like applying over power consumption, over current etc..

Features

- High endurance capability against to the short circuit.
- Built-in the over temperature shut-down circuit.
- Latch type shut down operation (need 0 voltage recovery).
- Built-in the current limitation circuit.

Outline

RENESAS Package code: PRSS0004AE-B
(Package name: LDKAK (S)-(1))



Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	-60	V
Gate to source voltage	V_{GSS}	-16	V
Gate to source voltage	V_{GSS}	2.5	V
Drain current	I_D	-50 ^{Note3}	A
Body-drain diode reverse drain current	I_{DR}	-50	A
Avalanche current	I_{AP} ^{Note 2}	-15	A
Avalanche energy	E_{AR} ^{Note 2}	964	mJ
Channel dissipation	P_{ch} ^{Note 1}	100	W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Notes: 1. Value at $T_c = 25^\circ\text{C}$
2. $T_{ch} = 25^\circ\text{C}$, $R_g \geq 50 \Omega$
3. It provides by the current limitation lower bound value.

Typical Operation Characteristics

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Input voltage	V_{IH}	-3.5	—	—	V	
	V_{IL}	—	—	-1.2	V	
Input current (Gate non shut down)	I_{IH1}	—	—	-100	μA	$V_i = -8 V, V_{DS} = 0$
	I_{IH2}	—	—	-50	μA	$V_i = -3.5 V, V_{DS} = 0$
Input current (Gate shut down)	$I_{IH(sd)1}$	—	-0.3	—	mA	$V_i = -12 V, V_{DS} = 0$
	$I_{IH(sd)2}$	—	-0.11	—	mA	$V_i = -4.6 V, V_{DS} = 0$
Shut down temperature	Tsd	—	175	—	°C	Channel temperature
Gate operation voltage	Vop	-3.5	—	-12	V	
Drain current (Current limitation value)	$I_{D \text{ limit}}$	-50	—	—	A	$V_{GS} = -12 V, V_{DS} = -10 V$ ^{Note 4}

Notes: 4. Pulse test

Electrical Characteristics

(Ta = 25°C)

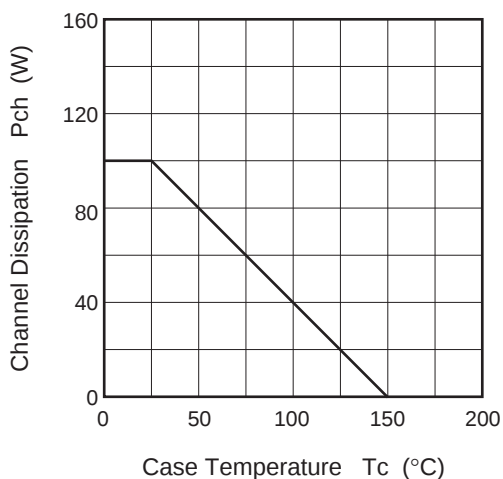
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain current	I_{D1}	—	—	-100	A	$V_{GS} = -3.5 V, V_{DS} = -10 V$
	I_{D2}	—	—	-10	mA	$V_{GS} = -1.2 V, V_{DS} = -10 V$
	I_{D3}	-50	—	—	A	$V_{GS} = -12 V, V_{DS} = -10 V$ ^{Note 5}
Drain to source breakdown voltage	$V_{(BR)DSS}$	-60	—	—	V	$I_D = -10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	-16	—	—	V	$I_G = -800 \mu A, V_{DS} = 0$
	$V_{(BR)GSS}$	2.5	—	—	V	$I_G = 100 \mu A, V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	-200	μA	$V_{GS} = -8 V, V_{DS} = 0$
	I_{GSS}	—	—	-800	μA	$V_{GS} = -16 V, V_{DS} = 0$
	I_{GSS}	—	—	100	μA	$V_{GS} = -2.4 V, V_{DS} = 0$
Input current (shut down)	$I_{GS(OP)1}$	—	-0.8	—	mA	$V_{GS} = -12 V, V_{DS} = 0$
	$I_{GS(OP)2}$	—	-0.11	—	mA	$V_{GS} = -4.6 V, V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	-10	μA	$V_{DS} = -60 V, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-3.4	—	-4.6	V	$V_{DS} = -10 V, I_D = -1 \text{ mA}$
Static drain to source on state resistance	$R_{DS(on)}$	—	16	30	m Ω	$I_D = -25 A, V_{GS} = -6 V$ ^{Note 5}
	$R_{DS(on)}$	—	12	15	m Ω	$I_D = -25 A, V_{GS} = -10 V$ ^{Note 5}
Output capacitance	Coss	—	1400	—	pF	$V_{DS} = -10 V, V_{GS} = 0, f = 1 \text{ MHz}$
Turn-on delay time	$t_{d(on)}$	—	77.2	—	μs	$V_{GS} = -10 V, I_D = -25 A, R_L = 1.2 \Omega$
Rise time	t_r	—	72.7	—	μs	
Turn-off delay time	$t_{d(off)}$	—	7.7	—	μs	
Fall time	t_f	—	7.7	—	μs	
Body-drain diode forward voltage	V_{DF}	—	-0.92	—	V	$I_F = -50 A, V_{GS} = 0$
Body-drain diode reverse recovery time	t_{rr}	—	133	—	ns	$I_F = -50 A, V_{GS} = 0$ $di_F/dt = 50 A/\mu s$
Over load shut down operation time ^{Note 6}	t_{os1}	—	6.3	—	ms	$V_{GS} = -5 V, V_{DD} = -16 V$

Notes: 5. Pulse test

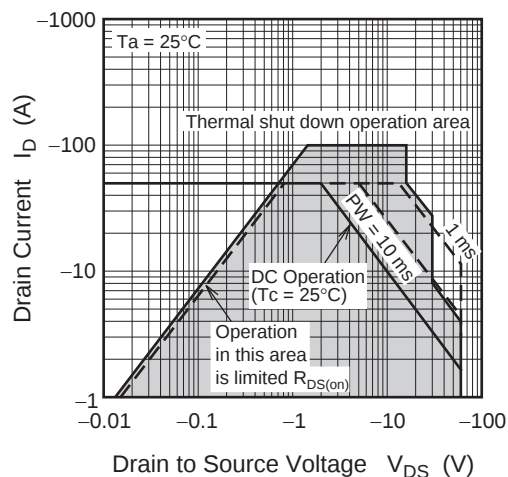
6. Including the junction temperature rise of the over loaded condition.

Main Characteristics

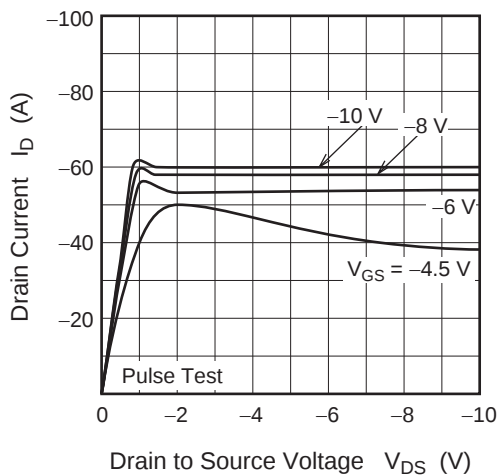
Power vs. Temperature Derating



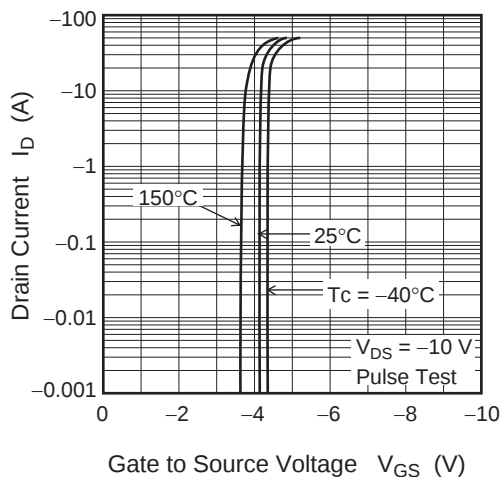
Maximum Safe Operation Area



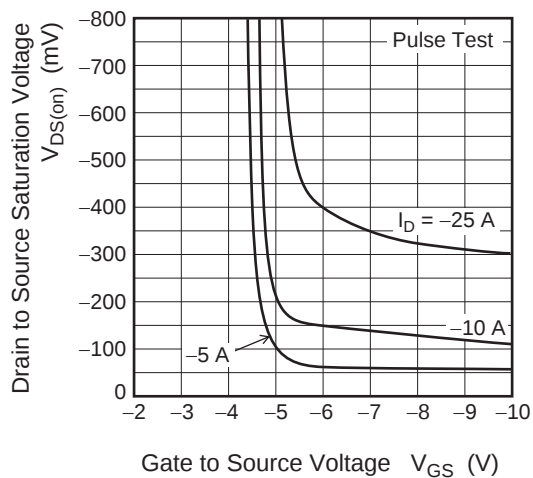
Typical Output Characteristics



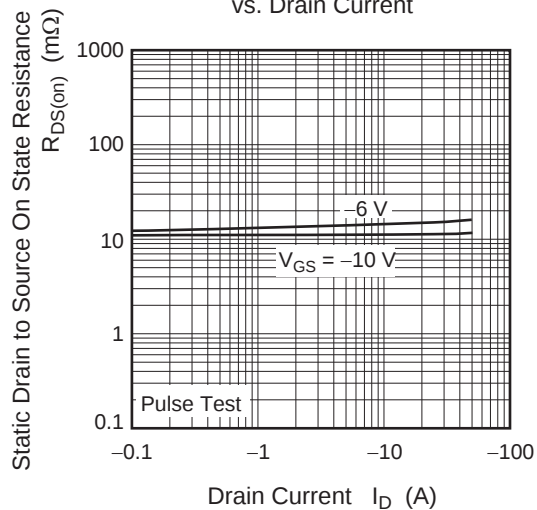
Typical Transfer Characteristics



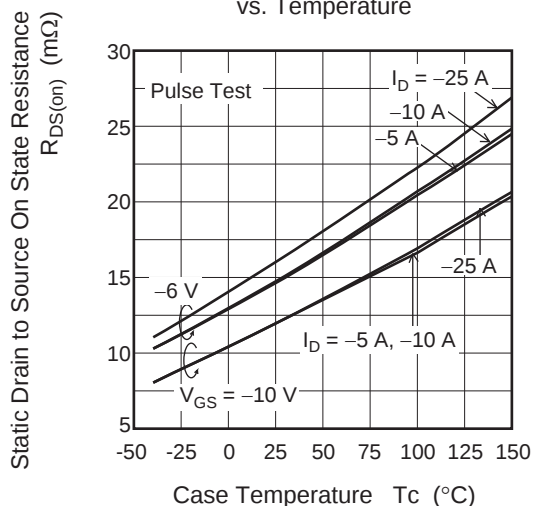
Drain Source Saturation Voltage vs. Gate to Source Voltage



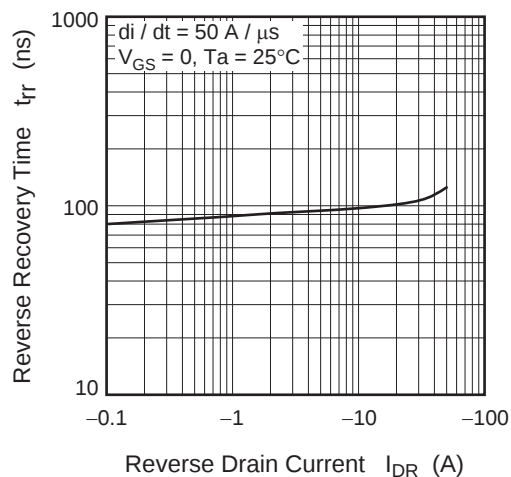
Static Drain to Source On State Resistance vs. Drain Current



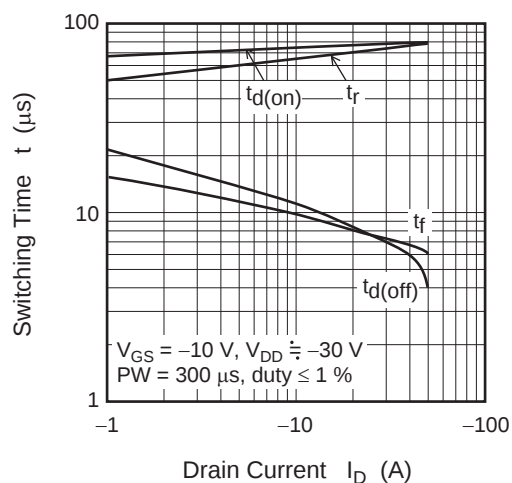
Static Drain to Source On State Resistance vs. Temperature



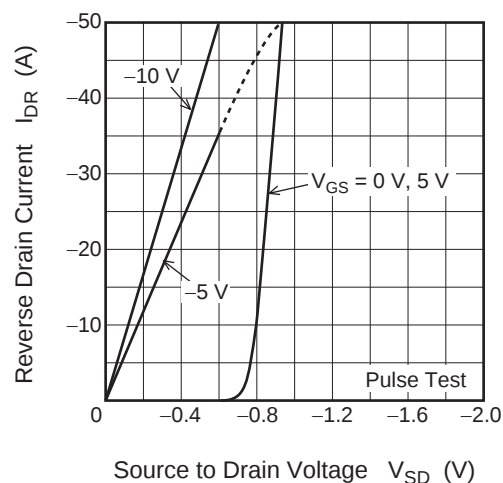
Body-Drain Diode Reverse Recovery Time



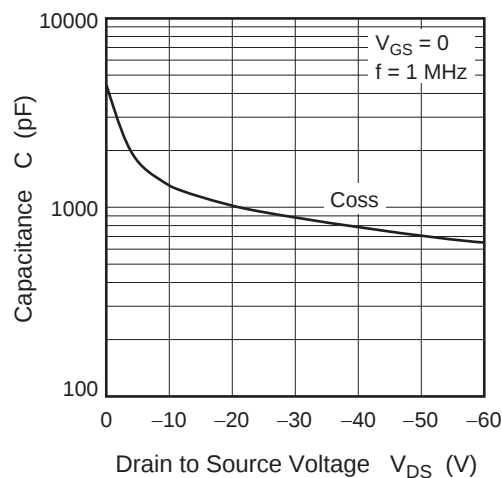
Switching Characteristics



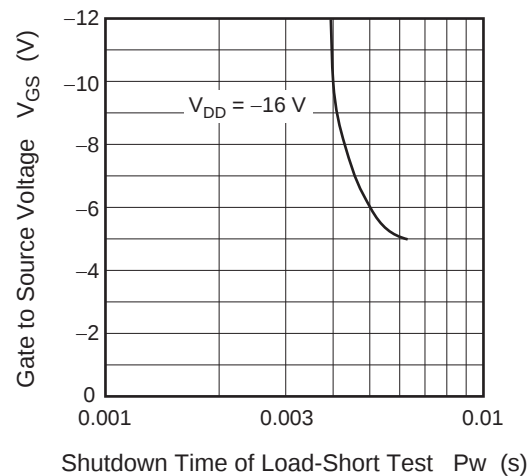
Reverse Drain Current vs. Source to Drain Voltage

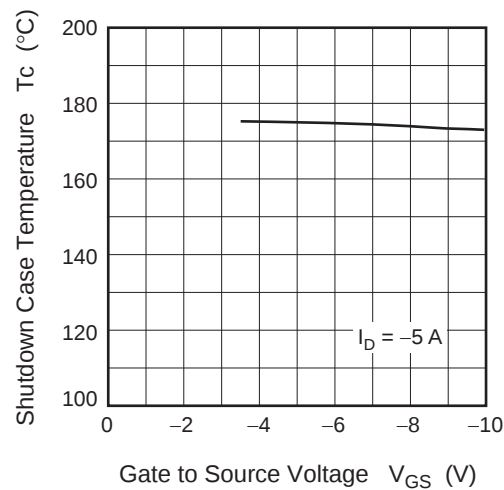


Typical Capacitance vs. Drain to Source Voltage

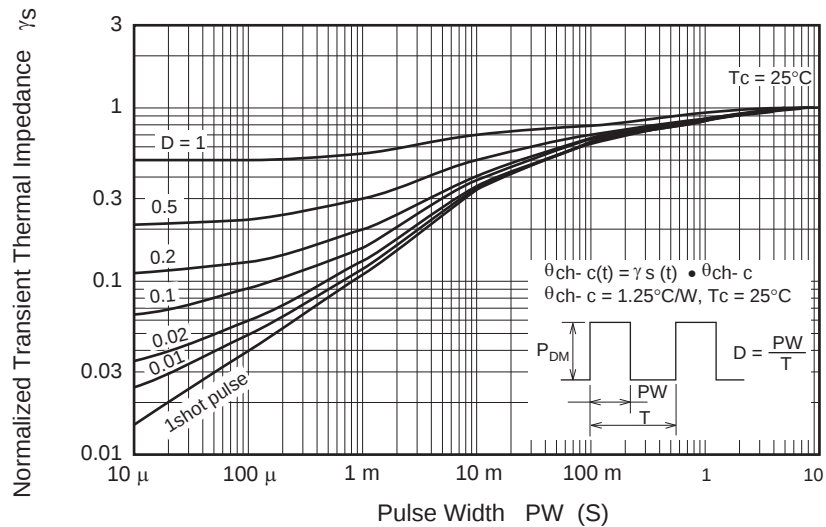


Gate to Source Voltage vs. Shutdown Time of Load-Short Test

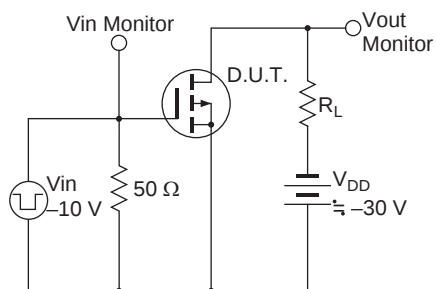


Shutdown Case Temperature vs.
Gate to Source Voltage

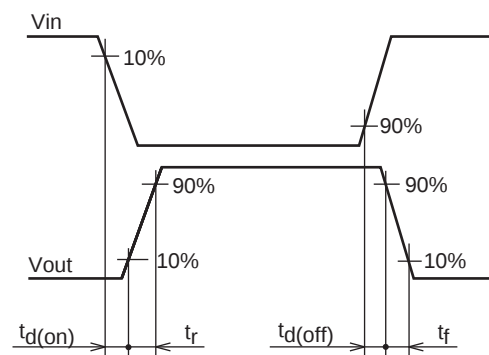
Normalized Transient Thermal Impedance vs. Pulse Width



Switching Time Test Circuit



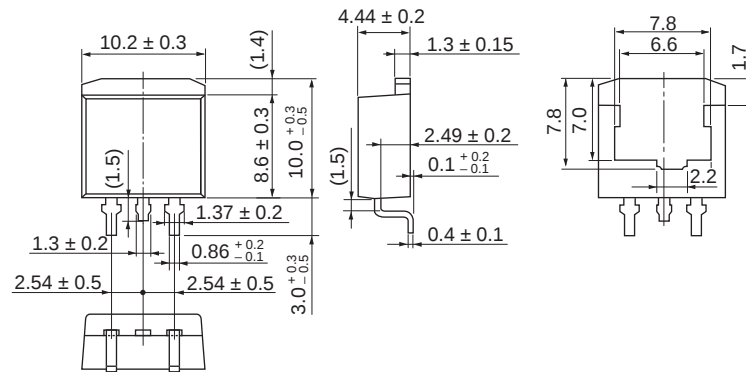
Waveform



Package Dimensions

Package Name	JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
LDBPAK(S)-(1)	SC-83	PRSS0004AE-B	LDBPAK(S)-(1) / LDBPAK(S)-(1)V	1.30g

Unit: mm



Ordering Information

Orderable Part No.	Quantity	Shipping Container
RJE0603JPE-00-J3	1000 pcs	Taping (Sinistrorse)

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Renesas Electronics America Inc.
2880 Scott Boulevard Santa Clara, CA 95050-2554, U.S.A.
Tel: +1-408-588-6000, Fax: +1-408-588-6130

Renesas Electronics Canada Limited
1101 Nicholson Road, Newmarket, Ontario L3Y 9C3, Canada
Tel: +1-905-898-5441, Fax: +1-905-898-3220

Renesas Electronics Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: +44-1628-585-100, Fax: +44-1628-585-900

Renesas Electronics Europe GmbH
Arcadiastrasse 10, 40472 Düsseldorf, Germany
Tel: +49-211-65030, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd.
7th Floor, Quantum Plaza, No.27 ZhiChunLu Haidian District, Beijing 100083, P.R.China
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

Renesas Electronics (Shanghai) Co., Ltd.
Unit 204, 205, AZIA Center, No.1233 Lujiazui Ring Rd., Pudong District, Shanghai 200120, China
Tel: +86-21-5877-1818, Fax: +86-21-6887-7858 / -7898

Renesas Electronics Hong Kong Limited
Unit 1601-1613, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong
Tel: +852-2886-9318, Fax: +852-2886-9022/9044

Renesas Electronics Taiwan Co., Ltd.
7F, No. 363 Fu Shing North Road Taipei, Taiwan
Tel: +886-2-8175-9600, Fax: +886-2-8175-9670

Renesas Electronics Singapore Pte. Ltd.
1 HarbourFront Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: +65-6213-0200, Fax: +65-6278-8001

Renesas Electronics Malaysia Sdn Bhd.
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: +60-3-7955-9390, Fax: +60-3-7955-9510

Renesas Electronics Korea Co., Ltd.
11F., Samik Laviel' or Bldg., 720-2 Yeoksam-Dong, Kangnam-Ku, Seoul 135-080, Korea
Tel: +82-2-558-3737, Fax: +82-2-558-5141